CLAIMS

1. A sputtering target material for producing an intermediate layer film of a perpendicular magnetic recording medium, comprising, in at %, 1 to 20% of W; 0.1 to 10% in total of one or more elements selected from the group consisting of P, Zr, Si and B; and balance Ni.

2. The sputtering target material according to claim 1, consisting of, in at %, 1 to 20% of W; 0.1 to 10% in total of one or more elements selected from the group consisting of P, Zr, Si and B; and balance Ni.

3. The sputtering target material according to claim 1, comprising, in at %, 1 to 20% of W; 0.1 to 10% in total of P and/or Zr; and balance Ni.

4. The sputtering target material according to claim 3, consisting of, in at %, 1 to 20% of W; 0.1 to 10% in total of P and/or Zr; and balance Ni.

5. The sputtering target material according to claim 3, obtained by consolidating a raw material powder produced by gas atomization.

6. A Ni-W-P, Zr-based thin film produced by using the sputtering target material according to claim 3.

7. The sputtering target material according to claim 1, comprising, in at %, 1 to 20% of W; 0.1 to 10% in total of Si and B; and balance Ni.

8. The sputtering target material according to claim 7, consisting of, in at %, 1 to 20% of W; 0.1 to 10% in total of Si and B; and balance Ni.

9. The sputtering target material according to claim 7, wherein the ratio of Si and B is 2:8 to 6:4.

10. The sputtering target material according to claim 9, obtained by consolidating a raw material powder produced by gas atomization.

11. The sputtering target material according to claim 7, obtained by consolidating at a temperature of 800°C or more and 1250°C or less.

12. A Ni-W-(Si, B)-based thin film produced by using the sputtering target material according to claim 7.

13. The sputtering target material according to claim 7, obtained by consolidating a raw material powder produced by gas atomization.

CLAIMS:

1. A sputtering target material for producing a Ni-W-(Si, B)-based intermediate layer film of a perpendicular magnetic recording medium, comprising, in at %, 1 to 20% of W; 0.1 to 10% in total of Si and B; and balance Ni.

2. The sputtering target material having the composition according to claim 1, wherein the ratio of Si and B is 2:8 to 6:4.

3. The sputtering target material according to claim 2, obtained by consolidating a raw material powder produced by gas atomization.

4. The sputtering target material according to claim 1 or 2, obtained by consolidating at a temperature of 800 °C or more and 1250 °C or less.